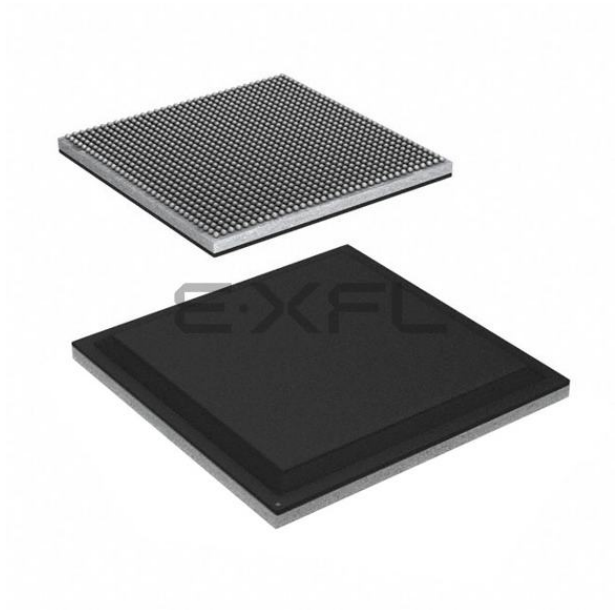

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 600MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 653K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1156-BBGA, FCBGA
Supplier Device Package	1156-FCBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu11eg-l1ffvc1156i

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.(12)	–	260	°C
T_j	Maximum junction temperature.(12)	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
Processor System					
$V_{CC\_PSINTFP}$(3)	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
$V_{CC\_PSINTLP}$	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
$V_{CC\_PSINTFP\_DDR}$(3)	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V_{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
$V_{PS\_MGTRAVCC}$	PS-GTR supply voltage.	0.825	0.850	0.875	V
$V_{PS\_MGTRAVTT}$	PS-GTR termination voltage.	1.746	1.800	1.854	V
V_{CCO_PSDDR}(4)	PS DDR I/O supply voltage.	1.06	–	1.575	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V_{CCO_PSIO}(5)	PS I/O supply.	1.710	–	3.465	V
V_{PSIN}	PS I/O input voltage.	–0.200	–	V_{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V_{CCO_PSDDR} + 0.200	
V_{CC_PSBATT}(6)	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V_{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(7)	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Available Speed Grades and Operating Voltages

Table 3 describes the speed grades per device and the V_{CCINT} operating supply voltages for the full-power, low-power, and DDR domains. For more information on selecting devices and speed grades, see the *UltraScale Architecture and Product Overview* (DS890).

Table 3: **Available Speed Grades and Operating Voltages**

Speed Grade	V_{CCINT}	$V_{CC\_PSINTLP}$	$V_{CC\_PSINTFP}$	$V_{CC\_PSINTFP\_DDR}$	Units
-3E	0.90	0.90	0.90	0.90	V
-2E	0.85	0.85	0.85	0.85	V
-2I	0.85	0.85	0.85	0.85	V
-2LE	0.85	0.85	0.85	0.85	V
-1E	0.85	0.85	0.85	0.85	V
-1I	0.85	0.85	0.85	0.85	V
-1LI	0.85	0.85	0.85	0.85	V
-2LE	0.72	0.85	0.85	0.85	V
-1LI	0.72	0.85	0.85	0.85	V

DC Characteristics Over Recommended Operating Conditions

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).(2)	–	–	15	µA
C_{IN}(3)	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCONPL}$	Analog supply current for the PL SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCONPS}$	Analog supply current for the PS SYSMON circuits in the power-up state.	–	–	10	mA
$I_{CCADCOFFPL}$	Analog supply current for the PL SYSMON circuits in the power-down state.	–	–	1.5	mA
$I_{CCADCOFFPS}$	Analog supply current for the PS SYSMON circuits in the power-down state.	–	–	1.8	mA

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: **Power-on Current by Device(1)**

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ}+	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
I_{CCINT_IOMIN}+ $I_{CCBRAMMIN}$	$I_{CCBRAMQ}$+ I_{CCINT_IOQ}+	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ}+	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}$+ I_{CCAUX_IOMIN}	I_{CCAUXQ}+ I_{CCAUX_IOQ}+	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: **Power Supply Ramp Time**

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT}.	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO}.	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU}.	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO}.	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX}.	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM}.	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC\_PSINTFP}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP}$.	0.2	40	ms
$T_{VCC\_PSINTLP}$	Ramp time from GND to 95% of $V_{CC\_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX}.	0.2	40	ms
$T_{VCC\_PSINTFP\_DDR}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP\_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC}.	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL}.	0.2	40	ms
$T_{PS\_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVCC}$.	0.2	40	ms
$T_{PS\_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVTT}$.	0.2	40	ms

Table 11: **Power Supply Ramp Time *(Cont'd)***

Symbol	Description	Min	Max	Units
T_{VCCO_PSDDR}	Ramp time from GND to 95% of V_{CCO_PSDDR}.	0.2	40	ms
$T_{VCC\_PSDDR\_PLL}$	Ramp time from GND to 95% of $V_{CC\_PSDDR\_PLL}$.	0.2	40	ms
T_{VCCO_PSIO}	Ramp time from GND to 95% of V_{CCO_PSIO}.	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

PS I/O Levels

Table 12: **PS MIO and CONFIG DC Input and Output Levels(1)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVCMOS33	–0.300	0.800	2.000	V_{CCO_PSIO}	0.40	2.40	12	–12
LVCMOS25	–0.300	0.700	1.700	V_{CCO_PSIO} + 0.30	0.70	1.70	12	–12
LVCMOS18	–0.300	35% V_{CCO_PSIO}	65% V_{CCO_PSIO}	V_{CCO_PSIO} + 0.30	0.45	V_{CCO_PSIO} – 0.45	12	–12

Notes:
1. Tested according to relevant specifications.

Table 13: **PS DDR DC Input and Output Levels(1)**

DDR Standard	V_{IL}		V_{IH}		V_{OL}(2)	V_{OH}(2)	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
DDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.8 x V_{CCO_PSDDR} – 0.150	0.8 x V_{CCO_PSDDR} + 0.150	10	–0.1
LPDDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.3 x V_{CCO_PSDDR} – 0.150	0.3 x V_{CCO_PSDDR} + 0.150	0.1	–10
DDR3	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.175	0.5 x V_{CCO_PSDDR} + 0.175	8	–8
LPDDR3	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8
DDR3L	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8

Notes:
1. Tested according to relevant specifications.
2. DDR4 V_{OL}/V_{OH} specifications are only applicable for DQ/DQS pins.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 26 correlates the current status of the Zynq UltraScale+ MPSoC on a per speed grade basis. See Table 3 for operating voltages listed by speed grade.

Table 26: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU2CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU2EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU4CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	**Preliminary**	**Production**
XCZU11EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU15EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU17EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU19EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Notes:

1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

PS Switching Characteristics

PS Clocks

Table 34: **PS Reference Clock Requirements**(1)

Symbol	Description	Min	Typ	Max	Units
$T_{RMSJPSCLK}$	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
$T_{PJPSCLK}$	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
$T_{DCPSCLK}$	PS_REF_CLK duty cycle.	45	–	55	%
$T_{RFPSCLK}$	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F_{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

1. The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: **PS RTC Crystal Requirements**(1)

Symbol	Description	Min	Typ	Max	Units
F_{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T_{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C_{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R_{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C_{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

1. Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C_1 and C_2 capacitance = 21 pF.

Table 36: **PS PLL Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{LOCKPSPLL}$	PLL maximum lock time.	100	100	100	µs
$F_{PSPLLMAX}$	PLL maximum output frequency.	1600	1600	1600	MHz
$F_{PSPLLMIN}$	PLL minimum output frequency.	750	750	750	MHz
$F_{PSPLLVCOMAX}$	PLL maximum VCO frequency.	3000	3000	3000	MHz
$F_{PSPLLVCOMIN}$	PLL minimum VCO frequency.	1500	1500	1500	MHz

PS Configuration

Table 39: **Processor Configuration Access Port Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{PCAPCK}	Maximum processor configuration access port (PCAP) frequency.	200	200	200	150	150	MHz

Table 40: **Boundary-Scan Port Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{TCK}	JTAG clock maximum frequency.	25	25	25	15	15	MHz
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup and hold.	4.0/2.0	4.0/2.0	4.0/2.0	5.0/2.0	5.0/2.0	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output.	16.1	16.1	16.1	24	24	ns, Max

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength.

Table 42: **Linear Quad-SPI Interface(1)**

Symbol	Description	Load Conditions(2)	Min	Max	Units
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
$T_{DCQSPICLK5}$	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
$T_{QSPISSSCLK5}$	Slave select asserted to next clock edge.(3)	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPISCLKSS5}$	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPICKO5}$	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
$T_{QSPIDCK5}$	Setup time, all inputs.	15 pF	2.4	–	ns
		30 pF	2.4	–	ns
$T_{QSPICKD5}$	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
$F_{QSPIREFCLK5}$	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz
$F_{QSPICLK5}$	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz

Notes:

1. The test conditions are configured for the linear Quad-SPI interface at 100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for stacked modes.
3. $T_{QSPISSSCLK5}$ is only valid when two reference clock cycles are programmed between chip select and clock.

PS USB Interface

Table 43: **ULPI Interface(1)**

Symbol	Description	Min	Max	Units
$T_{ULPIDCK}$	Input setup to ULPI clock, all inputs.	4.5	–	ns
$T_{ULPICKD}$	Input hold to ULPI clock, all inputs.	0	–	ns
$T_{ULPICKO}$	ULPI clock to output valid, all outputs.	2.0	8.86	ns
$F_{ULPICLK}$	ULPI reference clock frequency.	–	60	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

Programmable Logic (PL) Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Zynq UltraScale+ MPSoC. These values are subject to the same guidelines as the AC Switching Characteristics, page 22. In each table, the I/O bank type is either high performance (HP) or high density (HD).

Table 70: **LVDS Component Mode Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (OSERDES 4:1, 8:1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS TX SDR (OSERDES 2:1, 4:1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX DDR (ISERDES 1:4, 1:8)(1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS RX DDR	HD	0	250	0	250	0	250	0	250	0	250	Mb/s
LVDS RX SDR (ISERDES 1:2, 1:4)(1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX SDR	HD	0	125	0	125	0	125	0	125	0	125	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 71: **LVDS Native Mode Performance(1)(2)**

Description	DATA_WIDTH	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3(3)		-2(3)		-1		-2(3)		-1		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (TX_BITSLICE)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS TX SDR (TX_BITSLICE)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s
LVDS RX DDR (RX_BITSLICE)(4)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS RX SDR (RX_BITSLICE)(4)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s

Notes:

1. Native mode is supported through the High-Speed SelectIO Interface Wizard available with the Vivado Design Suite. The performance values assume a source-synchronous interface.
2. PLL settings can restrict the minimum allowable data rate. For example, when using the PLL with CLKOUTPHY_MODE = VCO_HALF the minimum frequency is PLL_F_{VCOMIN}/2.
3. In the SBVA484 package, the maximum data rate is 1260 Mb/s for DDR interfaces and 630 Mb/s for SDR interfaces.
4. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
HSTL_I_F	0.856	0.856	0.900	0.856	0.900	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
HSTL_I_S	0.856	0.856	0.900	0.856	0.900	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
HSUL_12_F	0.780	0.780	0.867	0.780	0.867	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
HSUL_12_S	0.780	0.780	0.867	0.780	0.867	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
LVCMOS12_F_12	0.918	0.918	0.976	0.918	0.976	1.689	1.689	1.856	1.689	1.856	1.202	1.202	1.317	1.202	1.317	ns
LVCMOS12_F_4	0.918	0.918	0.976	0.918	0.976	1.742	1.742	1.922	1.742	1.922	1.353	1.353	1.478	1.353	1.478	ns
LVCMOS12_F_8	0.918	0.918	0.976	0.918	0.976	1.714	1.714	1.879	1.714	1.879	1.292	1.292	1.432	1.292	1.432	ns
LVCMOS12_S_12	0.918	0.918	0.976	0.918	0.976	2.073	2.073	2.247	2.073	2.247	1.581	1.581	1.717	1.581	1.717	ns
LVCMOS12_S_4	0.918	0.918	0.976	0.918	0.976	1.979	1.979	2.182	1.979	2.182	1.633	1.633	1.772	1.633	1.772	ns
LVCMOS12_S_8	0.918	0.918	0.976	0.918	0.976	2.205	2.205	2.406	2.205	2.406	1.767	1.767	1.928	1.767	1.928	ns
LVCMOS15_F_12	0.905	0.905	0.958	0.905	0.958	1.713	1.713	1.892	1.713	1.892	1.275	1.275	1.428	1.275	1.428	ns
LVCMOS15_F_16	0.905	0.905	0.958	0.905	0.958	1.722	1.722	1.881	1.722	1.881	1.260	1.260	1.407	1.260	1.407	ns
LVCMOS15_F_4	0.905	0.905	0.958	0.905	0.958	1.825	1.825	1.959	1.825	1.959	1.453	1.453	1.557	1.453	1.557	ns
LVCMOS15_F_8	0.905	0.905	0.958	0.905	0.958	1.778	1.778	1.930	1.778	1.930	1.378	1.378	1.458	1.378	1.458	ns
LVCMOS15_S_12	0.905	0.905	0.958	0.905	0.958	1.991	1.991	2.139	1.991	2.139	1.516	1.516	1.648	1.516	1.648	ns
LVCMOS15_S_16	0.905	0.905	0.958	0.905	0.958	2.172	2.172	2.389	2.172	2.389	1.707	1.707	1.888	1.707	1.888	ns
LVCMOS15_S_4	0.905	0.905	0.958	0.905	0.958	2.313	2.313	2.483	2.313	2.483	1.952	1.952	2.123	1.952	2.123	ns
LVCMOS15_S_8	0.905	0.905	0.958	0.905	0.958	2.170	2.170	2.400	2.170	2.400	1.817	1.817	1.984	1.817	1.984	ns
LVCMOS18_F_12	0.915	0.915	0.958	0.915	0.958	1.805	1.805	1.962	1.805	1.962	1.383	1.383	1.471	1.383	1.471	ns
LVCMOS18_F_16	0.915	0.915	0.958	0.915	0.958	1.785	1.785	1.917	1.785	1.917	1.338	1.338	1.446	1.338	1.446	ns
LVCMOS18_F_4	0.915	0.915	0.958	0.915	0.958	1.868	1.868	2.013	1.868	2.013	1.472	1.472	1.599	1.472	1.599	ns
LVCMOS18_F_8	0.915	0.915	0.958	0.915	0.958	1.797	1.797	1.979	1.797	1.979	1.384	1.384	1.487	1.384	1.487	ns
LVCMOS18_S_12	0.915	0.915	0.958	0.915	0.958	2.201	2.201	2.408	2.201	2.408	1.762	1.762	1.894	1.762	1.894	ns
LVCMOS18_S_16	0.915	0.915	0.958	0.915	0.958	2.173	2.173	2.362	2.173	2.362	1.702	1.702	1.834	1.702	1.834	ns
LVCMOS18_S_4	0.915	0.915	0.958	0.915	0.958	2.346	2.346	2.567	2.346	2.567	1.951	1.951	2.092	1.951	2.092	ns
LVCMOS18_S_8	0.915	0.915	0.958	0.915	0.958	2.292	2.292	2.511	2.292	2.511	1.848	1.848	2.008	1.848	2.008	ns
LVCMOS25_F_12	0.988	0.988	1.042	0.988	1.042	2.153	2.153	2.453	2.153	2.453	1.692	1.692	1.856	1.692	1.856	ns
LVCMOS25_F_16	0.988	0.988	1.042	0.988	1.042	2.105	2.105	2.406	2.105	2.406	1.623	1.623	1.786	1.623	1.786	ns
LVCMOS25_F_4	0.988	0.988	1.042	0.988	1.042	2.344	2.344	2.554	2.344	2.554	1.842	1.842	2.039	1.842	2.039	ns
LVCMOS25_F_8	0.988	0.988	1.042	0.988	1.042	2.184	2.184	2.516	2.184	2.516	1.726	1.726	1.910	1.726	1.910	ns
LVCMOS25_S_12	0.988	0.988	1.042	0.988	1.042	2.558	2.558	2.840	2.558	2.840	1.971	1.971	2.194	1.971	2.194	ns
LVCMOS25_S_16	0.988	0.988	1.042	0.988	1.042	2.449	2.449	2.740	2.449	2.740	1.852	1.852	2.063	1.852	2.063	ns
LVCMOS25_S_4	0.988	0.988	1.042	0.988	1.042	2.770	2.770	3.066	2.770	3.066	2.224	2.224	2.458	2.224	2.458	ns
LVCMOS25_S_8	0.988	0.988	1.042	0.988	1.042	2.663	2.663	2.963	2.663	2.963	2.091	2.091	2.373	2.091	2.373	ns
LVCMOS33_F_12	1.154	1.154	1.213	1.154	1.213	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVCMOS33_F_16	1.154	1.154	1.213	1.154	1.213	2.383	2.383	2.603	2.383	2.603	1.734	1.734	1.869	1.734	1.869	ns
LVCMOS33_F_4	1.154	1.154	1.213	1.154	1.213	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVCMOS33_F_8	1.154	1.154	1.213	1.154	1.213	2.603	2.603	2.822	2.603	2.822	1.937	1.937	2.130	1.937	2.130	ns
LVCMOS33_S_12	1.154	1.154	1.213	1.154	1.213	2.705	2.705	3.047	2.705	3.047	2.049	2.049	2.318	2.049	2.318	ns
LVCMOS33_S_16	1.154	1.154	1.213	1.154	1.213	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVCMOS33_S_4	1.154	1.154	1.213	1.154	1.213	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
LVCMOS33_S_8	1.154	1.154	1.213	1.154	1.213	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
LVDS_25	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVTTL_F_12	1.164	1.164	1.223	1.164	1.223	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVTTL_F_16	1.164	1.164	1.223	1.164	1.223	2.464	2.464	2.732	2.464	2.732	1.750	1.750	1.986	1.750	1.986	ns
LVTTL_F_4	1.164	1.164	1.223	1.164	1.223	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVTTL_F_8	1.164	1.164	1.223	1.164	1.223	2.582	2.582	2.787	2.582	2.787	1.910	1.910	2.063	1.910	2.063	ns
LVTTL_S_12	1.164	1.164	1.223	1.164	1.223	2.731	2.731	3.075	2.731	3.075	2.072	2.072	2.343	2.072	2.343	ns
LVTTL_S_16	1.164	1.164	1.223	1.164	1.223	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVTTL_S_4	1.164	1.164	1.223	1.164	1.223	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns
LVTTL_S_8	1.164	1.164	1.223	1.164	1.223	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
SLVS_400_25	1.020	1.020	1.136	1.020	1.136	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_F	0.780	0.780	0.867	0.780	0.867	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
SSTL12_S	0.780	0.780	0.867	0.780	0.867	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
SSTL135_F	0.798	0.798	0.881	0.798	0.881	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
SSTL135_II_F	0.798	0.798	0.881	0.798	0.881	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
SSTL135_II_S	0.798	0.798	0.881	0.798	0.881	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
SSTL135_S	0.798	0.798	0.881	0.798	0.881	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
SSTL15_F	0.838	0.838	0.880	0.838	0.880	1.612	1.612	1.754	1.612	1.754	1.357	1.357	1.464	1.357	1.464	ns
SSTL15_II_F	0.838	0.838	0.880	0.838	0.880	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
SSTL15_II_S	0.838	0.838	0.880	0.838	0.880	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
SSTL15_S	0.838	0.838	0.880	0.838	0.880	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
SSTL18_II_F	0.947	0.947	1.021	0.947	1.021	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
SSTL18_II_S	0.947	0.947	1.021	0.947	1.021	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
SSTL18_I_F	0.947	0.947	1.021	0.947	1.021	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
SSTL18_I_S	0.947	0.947	1.021	0.947	1.021	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
SUB_LVDS	1.002	1.002	1.036	1.002	1.036	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns

Table 91: **Global Clock Input Setup and Hold With MMCM**

Symbol	Description		Device	Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
				-3	-2	-1	-2	-1	
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
$T_{PSMMCMCC\_ZU2}$	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU2}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU3}$		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU3}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU4}$		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU4}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU5}$		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU5}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU6}$		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU6}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU7}$		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
$T_{PHMMCMCC\_ZU7}$		Hold		–0.14	–0.14	–0.14	0.37	0.38	ns
$T_{PSMMCMCC\_ZU9}$		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU9}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU11}$		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
$T_{PHMMCMCC\_ZU11}$		Hold		–0.08	–0.08	0.04	0.35	0.74	ns
$T_{PSMMCMCC\_ZU15}$		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU15}$		Hold		–0.10	–0.10	–0.10	0.17	0.19	ns
$T_{PSMMCMCC\_ZU17}$		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU17}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns
$T_{PSMMCMCC\_ZU19}$		Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU19}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

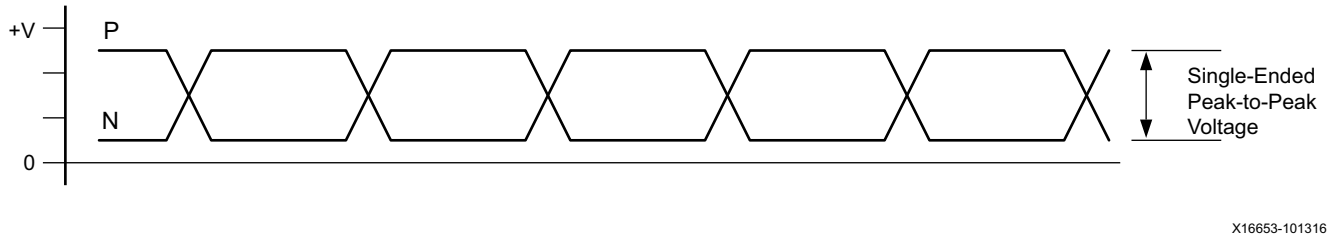

Figure 5: **Single-Ended Peak-to-Peak Voltage**

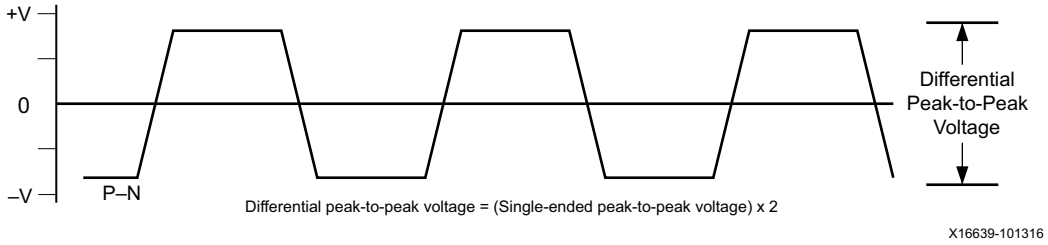

Figure 6: **Differential Peak-to-Peak Voltage**

Table 107 and Table 108 summarize the DC specifications of the clock input of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 107: **GTY Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	10	–	nF

Table 108: **GTY Transceiver Clock Output Level Specification**

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N	R_T = 100Ω across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N	R_T = 100Ω across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage (P–N), P = High (N–P), N = High	R_T = 100Ω across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage	R_T = 100Ω across P and N signals	300	–	500	mV

Table 116: **GTY Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTYRX}	Serial data rate		0.500	–	F_{GTYMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T\_SJ32.75}$	Sinusoidal jitter (QPLL)(3)	32.75 Gb/s	0.25	–	–	UI
$J_{T\_SJ28.21}$	Sinusoidal jitter (QPLL)(3)	28.21 Gb/s	0.30	–	–	UI
$J_{T\_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T\_SJ15.0}$	Sinusoidal jitter (QPLL)(3)	15.0 Gb/s	0.30	–	–	UI
$J_{T\_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T\_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ8.0}$	Sinusoidal jitter (CPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T\_SJ6.6}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T\_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T\_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T\_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI
$J_{T\_SJ2.5}$	Sinusoidal jitter (CPLL)(3)	2.5 Gb/s(5)	0.30	–	–	UI
$J_{T\_SJ1.25}$	Sinusoidal jitter (CPLL)(3)	1.25 Gb/s(6)	0.30	–	–	UI
J_{T_SJ500}	Sinusoidal jitter (CPLL)(3)	500 Mb/s(7)	0.30	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$J_{T\_TJSE3.2}$	Total jitter with stressed eye(8)	3.2 Gb/s	0.70	–	–	UI
$J_{T\_TJSE6.6}$		6.6 Gb/s	0.70	–	–	UI
$J_{T\_SJSE3.2}$	Sinusoidal jitter with stressed eye(8)	3.2 Gb/s	0.10	–	–	UI
$J_{T\_SJSE6.6}$		6.6 Gb/s	0.10	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of 10^{-12}.
3. The frequency of the injected sinusoidal jitter is 80 MHz.
4. CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
7. CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
8. Composite jitter with RX equalizer enabled. DFE disabled.

GTY Transceiver Electrical Compliance

The *UltraScale Architecture GTY Transceiver User Guide* (UG578) contains recommended use modes that ensure compliance for the protocols listed in Table 117. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 117: **GTY Transceiver Protocol List**

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-4	IEEE 802.3-2012	25.78125	Compliant
28 Gb/s backplane	CEI-25G-LR	25–28.05	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11GSR, OIF-CEI-28G-MR	4.25–25.78125	Compliant
100GBASE-KR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
100GBASE-CR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
OTU4 (OTL4.4) CFP2	OIF-CEI-28G-VSR	27.952493–32.75	Compliant
OTU4 (OTL4.4) CFP	OIF-CEI-11G-MR	11.18–13.1	Compliant
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR(2)	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
QSGMII	QSGMII v1.2 (Cisco System, ENG-46158)	5	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI(3)	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI(3)	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys bandwidth engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
Passive optical network (PON)	10G-EPON, 1G-EPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant

Configuration Switching Characteristics

Table 127: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
PL Power-up Timing Characteristics							
T_{PL}	PS_PROG_B PL latency.	7.5	7.5	7.5	7.5	7.5	ms, Max
T_{POR}	Power-on reset from PL power-on to PL ready to configure (40 ms maximum ramp rate).	65	65	65	65	65	ms, Max
		0	0	0	0	0	ms, Min
	Power-on reset from PL power-on to PL ready to configure with POR override (2 ms maximum ramp rate).	15	15	15	15	15	ms, Max
		5	5	5	5	5	ms, Min
$T_{PS\_PROG\_B}$	PL program pulse width.	250	250	250	250	250	ns, Min
Internal Configuration Access Port							
F_{ICAPCK}	Internal configuration access port (ICAPE3).	200	200	200	150	150	MHz, Max
DNA Port Switching							
F_{DNACK}	DNA port frequency (DNA_PORT).	200	200	200	175	175	MHz, Max
STARTUPE3 Ports							
$F_{CFGMCLK}$	STARTUPE3 CFGMCLK output frequency.	50.00	50.00	50.00	50.00	50.00	MHz, Typ
$F_{CFGMCLKTOL}$	STARTUPE3 CFGMCLK output frequency tolerance.	±15	±15	±15	±15	±15	%, Max
T_{DCI_MATCH}	Specifies a stall in the startup cycle until the digitally controlled impedance (DCI) match signals are asserted.	4	4	4	4	4	ms, Max

Date	Version	Description of Revisions
02/10/2017	1.2	Updated some of the maximum voltages in the Processor System (PS) section and other specifications in the Programmable Logic (PL) and GTH or GTY Transceiver sections of Table 1. Updated Table 2, Table 4, Table 6, Table 7, and Table 9. Revised the Power Supply Sequencing section including Table 10. Added PS and VCU ramp times to Table 11. Revised V_{ODIFF} in Table 24. Updated Table 25. Added Note 1 to Table 26. Table 30 replaces the previous three PS memory performance tables. Added values to Table 34, Table 37, and Table 38. Deleted the waveforms in the PS Switching Characteristics section (Figures 1-16 and Figures 25-26). Revised values in the *PS NAND Memory Controller Interface* section. Added and updated data in Table 40. Added Note 3 to Table 41. Added Note 3 to Table 42. Added Note 1 to Table 45. Updated Table 48 and removed Note 3. Added data to Table 56. Updated Table 60. Added Table 61. Updated Table 63. Revised Table 69. Added data to Table 70. Added Note 2 to Table 71. Updated Table 74 and added Note 4. Updated V_L and V_H values in Table 78. Added T_{MINPER_CLK}, revised F_{REFCLK}, and Note 1 to Table 82. Added MMCM_F_{DPRCLK_MAX} to Table 85 and PLL_F_{DPRCLK_MAX} to Table 86. Added data to Table 94, Table 96, Table 98, Table 101, and updated the note references in Table 102. Updated Table 103 and added Note 8. Updated Table 104 and added Note 7. Added more protocols, Note 1 and Note 2 to Table 105. Removed the *GTH Transceiver Protocol Jitter Characteristics* section because it is covered in Table 105. Added Note 1 to Table 109. Added data to Table 106, Table 108, Table 110, Table 113. Added Note 2 to Table 112. Added note references in Table 114. Updated Table 115 and added Note 8. Updated Table 116 and added Note 7. Added more protocols and Note 3 to Table 117. Removed the *GTY Transceiver Protocol Jitter Characteristics* section because it is covered in Table 117. Revised Table 124. Added T_{POR} and updated F_{ICAPCK} in Table 127. Updated the Automotive Applications Disclaimer.
06/20/2016	1.1	Updated the Summary description. In Table 1, revised V_{IN} for HP I/O banks and added clarifications to some descriptions and symbols. Added I_{RPU}, I_{RPD}, and Note 4 to Table 2 and updated $V_{PS\_MGTRAVCC}$, the PL System Monitor section, and Note 3 and Note 5. Updated Note 5 in Table 4. Updated the PS Power-On/Off Power Supply Sequencing section including all the voltage supply names. Added MIPI_DPHY_DCI to Table 14, Table 15, and Table 17. Updated Table 23, including removing the V_{CCO} specification and adding Note 1. Added Note 1 to Table 24. Updated Table 25 speed specifications for Vivado Design Suite 2016.1. Added values to Table 28. Updated the -2 value in Table 29. Added $F_{DPLIVEVIDEO}$ and updated $F_{FCIDMACLK}$ in Table 33. Added VCO frequencies to Table 36. Added the T_{PSPOR} minimum to Table 37 and updated Note 1. Added Table 38. Added value delineation over V_{CCINT} operating voltages in Table 39. Revised values for F_{TCK} and T_{TAPTCK}/T_{TCKTAP} in Table 40 and added value delineation over V_{CCINT} operating voltages. Updated the *PS NAND Memory Controller Interface* section. Revised some units and Note 1 in Table 41 and Table 42. Removed Figure 6: Quad-SPI Interface (Feedback Clock Disabled) Timing. Updated Note 1 of Table 43. Added $F_{TSI\_REF\_CLK}$ to Table 44 and updated Note 1. In Table 45, revised $T_{DCSDHSCLK1}$, $T_{DCSDHSCLK2}$, and $T_{DCSDHSCLK3}$ and Note 1. In Table 46, revised Note 1. In Table 47, revised Note 1. Revised Table 48, including Note 1, and added Note 2 and Note 3. In Table 49, Table 50, Table 51, and Table 53, revised Note 1. Updated Table 71. Replaced Table 74. Updated Table 75 and Table 76. Updated Table 78 and Table 79. In Table 80, added the Block RAM and FIFO Clock-to-Out Delays section. Updated the R_{IN} and C_{EXT} values in Table 57 and Table 95. Updated the -2 (0.72V) and -1 (0.72V) values and added Note 1 to Table 97. Added Table 100 and Table 112. Added Note 2 to Table 106. Revised data in Table 109. Revised Table 114. Revised data and added notes in the Integrated Interface Block for Interlaken section and Table 121. Moved Table 123. Revised INL in Table 124. Added notes to Table 125 and Table 126. In the *eFUSE and Programming Conditions* table, updated the I_{PSFS} description.
11/24/2015	1.0	Initial Xilinx release.